



IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/772,932 Filing Date: February 4, 2004
Confirmation No.: 6068
First Named Inventor: Chia-Shun Hsiao
Assignee: ProMOS Technologies Inc.
Examiner: Tran, Long K. Art Unit: 2818
Attorney Docket No.: M-15327 US

San Jose, California
June 7, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed except for United States Patents and United States Published Applications.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
 2. a representation that a search has been made, other than as described above;
- or
3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on June 7, 2005.

Michael Shenker 6-7-05
Attorney for Applicant(s) Date of Signature

Respectfully submitted,

Michael Shenker

Michael Shenker
Patent Attorney
Reg. No. 34,250
Telephone: (408) 392-9250

Law Offices Of
MacPherson Kwok Chen & Heid LLP
1762 Technology Drive, Suite 226
San Jose, CA 95110



U.S. Department of Commerce, Patent and Trademark Office					Atty. Docket No.		Serial No.	
					M-15327 US		10/772,932	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant(s)			
(Use several sheets if necessary)					Chia-Shun Hsiao et al.			
					Filing Date		Group	
					Feb. 4, 2004		2818	
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,403,417	06-2002	Chien et al.				
	AB	6,451,708	09-2002	Ha				
	AC							
	AD							
	AF							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
	AL	Naruke, K.; Yamada, S.; Obi, E.; Taguchi, S.; and Wada, M. "A New Flash-Erase EEPROM Cell with A Sidewall Select-Gate On Its Source Side," 1989 IEEE, pp. 604-606.						
	AM	Wu, A.T.; Chan T.Y.; Ko, P.K.; and Hu, C. "A Novel High-Speed, 5-Volt Programming EPROM Structure With Source-Side Injection," 1986 IEEE, 584-587.						
	AN	Mizutani, Yoshihisa; and Makita, Koji "A New EPROM Cell With A Sidewall Floating Gate Fro High-Density and High Performance Device," 1985 IEEE, 635-638.						
	AO	Ma, Y.; Pang, C.S.; Pathak, J.; Tsao, S.C.; Chang, C.F.; Yamauchi, Y.; Yoshimi, M. "A Novel High Density Contactless Flash Memory Array Using Split-Gate Source-Side-Injection Cell for 5V-Only Applications," 1994 Symposium on VLSI Technology Digest of Technical Papers, pp. 49-50.						
	AP	Mih, Rebecca et al. "0.18um Modular Triple Self-Aligned Embedded Split-Gate Flash Memory," 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 120-121.						
	AQ							
	AR							
Examiner				Date Considered				
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.</p>								